

# MOS FIELD EFFECT TRANSISTOR 2SK3424

# SWITCHING N-CHANNEL POWER MOS FET INDUSTRIAL USE

#### **DESCRIPTION**

The 2SK3424 is N-Channel MOS FET device that features a low on-state resistance and excellent switching characteristics, designed for low voltage high current applications such as DC/DC converter with synchronous rectifier.

#### **FEATURES**

- 4.5 V drive available
- Low on-state resistance  $R_{DS(on)1} = 11.5 \text{ m}\Omega \text{ MAX}. \text{ (Vgs} = 10 \text{ V, Ip} = 24 \text{ A)}$
- Low gate charge
   Q<sub>G</sub> = 34 nC TYP. (I<sub>D</sub> = 48 A, V<sub>DD</sub> = 24 V, V<sub>GS</sub> = 10 V)
- · Built-in gate protection diode
- · Surface mount device available

## ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (Ves = 0 V)	VDSS	30	V
Gate to Source Voltage (Vps = 0 V)	Vgss	±20	V
Drain Current (DC) (Tc = 25°C)	I <sub>D(DC)</sub>	±48	Α
Drain Current (Pulse) Note	D(pulse)	±192	Α
Total Power Dissipation (T <sub>A</sub> = 25°C)	P <sub>T1</sub>	1.5	W
Total Power Dissipation (Tc = 25°C)	P <sub>T2</sub>	50	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C

**Note** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

# ORDERING INFORMATION

PART NUMBER	PACKAGE		
2SK3424	TO-220AB		
2SK3424-ZK	TO-263(MP-25ZK)		
2SK3424-ZJ	TO-263(MP-25ZJ)		

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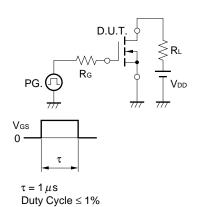


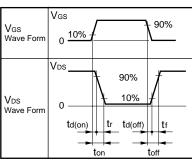
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# ELECTRICAL CHARACTERISTICS(TA = 25°C)

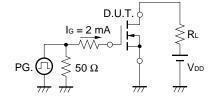
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Leakage Current	Ioss	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			10	μΑ
Gate Leakage Current	Igss	Vgs = ±20 V, Vps = 0 V			±10	μΑ
Gate Cut-off Voltage	V <sub>G</sub> S(off)	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	1.5		2.5	V
Forward Transfer Admittance	yfs	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 24 A	13			S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 10 V, ID = 24 A		7.7	11.5	mΩ
	R <sub>DS(on)2</sub>	Vgs = 4.5 V, ID = 24 A		10.5	17.0	mΩ
Input Capacitance	Ciss	Vps = 10 V		1900		pF
Output Capacitance	Coss	V <sub>G</sub> S = 0 V		580		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		270		pF
Turn-on Delay Time	td(on)	VDD = 15 V , ID = 24 A		14		ns
Rise Time	tr	V <sub>GS(on)</sub> = 10 V		13		ns
Turn-off Delay Time	td(off)	R <sub>G</sub> = 10 Ω		61		ns
Fall Time	tr			22		ns
Total Gate Charge	Q <sub>G</sub>	VDD = 24 V		34		nC
Gate to Source Charge	Qgs	Vgs = 10 V		6.4		nC
Gate to Drain Charge	Q <sub>GD</sub>	ID = 48 A		9.1		nC
Diode Forward Voltage	VF(S-D)	IF = 48 A, VGS = 0 V		1.0		V
Reverse Recovery Time	trr	IF = 48 A, VGS = 0 V		34		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		26		nC

## **TEST CIRCUIT 1 SWITCHING TIME**



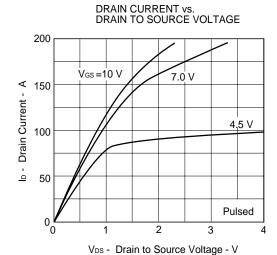


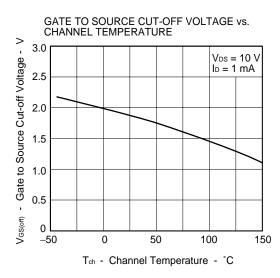
## **TEST CIRCUIT 2 GATE CHARGE**

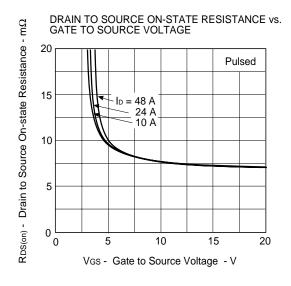




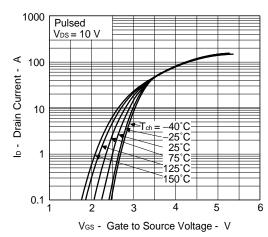
# 



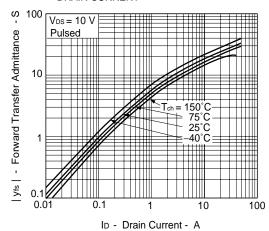




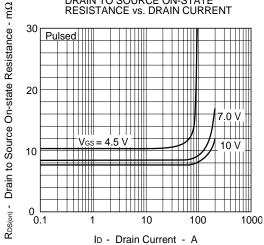




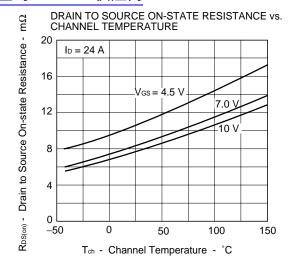
#### FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



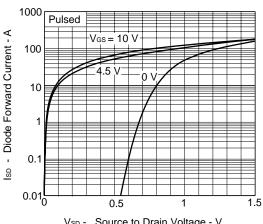
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



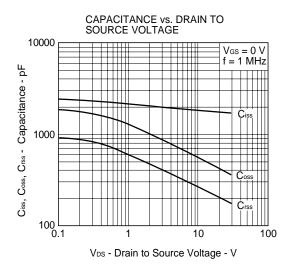
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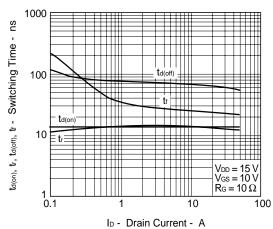
#### SOURCE TO DRAIN DIODE FORWARD VOLTAGE



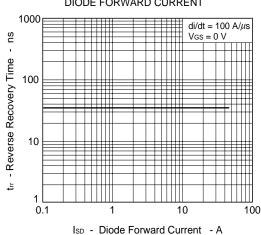
#### VsD - Source to Drain Voltage - V



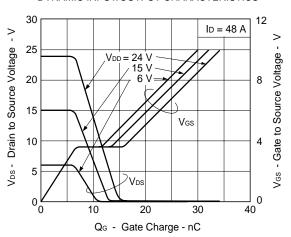
#### SWITCHING CHARACTERISTICS



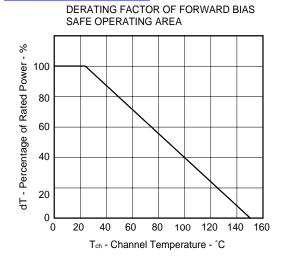
#### REVERSE RECOVERY TIME vs. DIODE FORWARD CURRENT

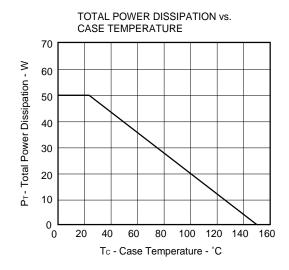


#### DYNAMIC INPUT/OUTPUT CHARACTERISTICS

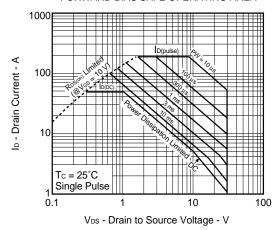


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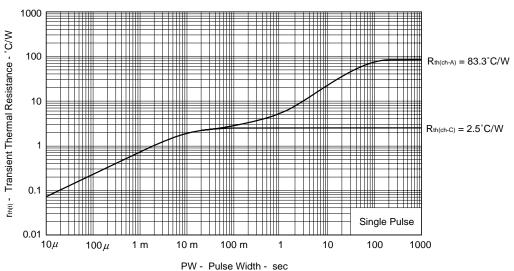




#### FORWARD BIAS SAFE OPERATING AREA



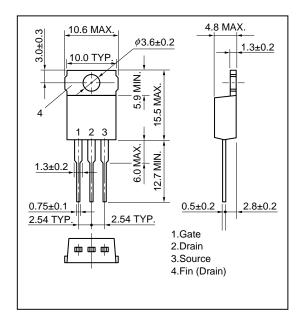
### TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



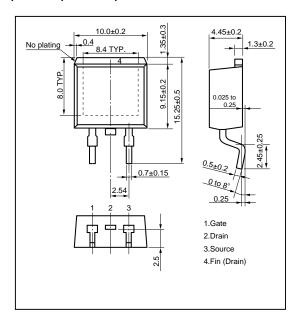


# PACK ACE DRAWING (Unit:mm)

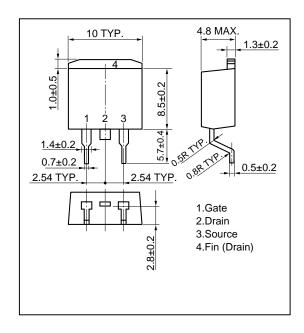
## ★ 1)TO-220AB (MP-25)



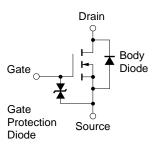
#### 2)TO-263 (MP-25ZK)



## ★ 3)TO-263 (MP-25ZJ)



### **EQUIVALENT CIRCUIT**



**Remark** The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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